


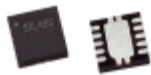
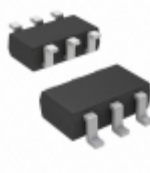




	<p>SI3464DV-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI3464DV-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 8A 6-TSOP</p> <p>Datenblätter:  SI3464DV-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 108443 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3464DV-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 8A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	108443 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	2W (Ta), 3.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Tc)
Rds On (Max) @ Id, Vgs	24 mOhm @ 7.5A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	18nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	1065pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)










































SI3464DV-T1-GE3 ist neu im Original, Suche SI3464DV-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3464DV-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3464DV-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3467DV VISHAY SI3467DV VISHAY</p>	 <p>Si3464DV Vishay Si3464DV Vishay</p>	 <p>SI3462-E01-GMR Energy Micro (Silicon Labs) IC POE/POE PSE SGL PORT 11-QFN</p>	 <p>SI3465DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 3A 6-TSOP</p>
 <p>SI3464DV-T1-E3 Son Son TSOP-6</p>	 <p>SI3464DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 8A 6-TSOP</p>	 <p>SI3462-EVB Energy Micro (Silicon Labs) BOARD EVAL POE PSE SGL PORT</p>	 <p>SI3465DV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 3A 6-TSOP</p>

heiße Teile

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|  SI3459BDV-T1-E3 |  SI3459BDV-T1-E3 |  SI3459BDV-T1-GE3 |  SI3459BDV-T1-GE3 |  SI3459DV-T1-E3 |
|  SI3459DV-T1-E3 |  SI3459DV-T1-GE3 |  SI3460-E02-GMR |  SI3460-E03-GMR |  SI3460BDV-T1-E3 |
|  SI3460BDV-T1-E3 |  SI3460BDV-T1-GE3 |  SI3460BDV-T1-GE3 |  SI3460DDV |  SI3460DDV-T1-GE3 |
|  SI3460DDV-T1-GE3 |  SI3460DV |  SI3460DV-T1 |  SI3460DV-T1-E3 |  SI3460DV-T1-E3 |
|  SI3460DV-T1-GE3 |  SI3460DV-T1-GE3 |  SI3461DV-T1-E3 |  SI3461DVT1-GE3 |  SI3464DV |
|  SI3464DV-T1-GE3 |  SI3465DV-T1-E3 |  SI3465DV-T1-E3 |  SI3465DV-T1-GE3 |  SI3465DV-T1-GE3 |
|  SI3467DV |  SI3467DV-T1-E3 |  SI3467DV-T1-E3 |  SI3467DV-T1-GE3 |  SI3467DV-T1-GE3 |
|  SI3469DV-T1 |  SI3469DV-T1-E3 |  SI3469DV-T1-E3 |  SI3469DV-T1-GE3 |  SI3469DV-T1-GE3 |
|  SI3471DV-T1-E3 |  SI3473CDV-T1-E3 |  SI3473CDV-T1-E3 |  SI3473CDV-T1-GE3 |  SI3473CDV-T1-GE3 |
|  SI3473DDV-T1-GE3 |  SI3473DV-T1-E3 |  SI3473DV-T1-E3 |  SI3473DV-T1-GE3 |  SI3473DV-T1-GE3 |

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